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(54) **NONVOLATILE MEMORY DEVICE AND  
MEMORY SYSTEM INCLUDING THE SAME**

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(71) Applicant: **Samsung Electronics Co., Ltd.,**  
Suwon-si (KR)

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(73) Assignee: **Samsung Electronics Co., Ltd.,**  
Suwon-si (KR)

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**ABSTRACT**

A nonvolatile memory device includes a peripheral circuit structure including a peripheral circuit and a first insulating structure covering the peripheral circuit and a cell array structure bonded to the peripheral circuit structure and including a cell region and a connection region, wherein the cell array structure includes a common source line layer, a buffer insulating layer on the common source line layer, a plurality of contact stop layers buried in the buffer insulating layer, a cell stack which includes a plurality of gate electrodes and a plurality of insulating layers alternately stacked on the buffer insulating layer, a plurality of cell channel structures extending to the common source line layer by passing through the cell stack, a plurality of contact structures each connected to one or more of the plurality of gate electrodes, and a second insulating structure covering the cell stack.

